

CSD18532Q5B 60V N-Channel NexFET™ Power MOSFETs

1 Features

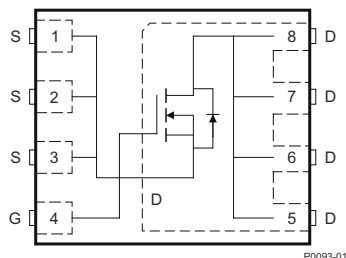
- Ultra-low Q_g and Q_{gd}
- Low thermal resistance
- Avalanche rated
- Logic level
- Lead-free terminal plating
- RoHS compliant
- Halogen free
- SON 5mm × 6mm plastic package

2 Applications

- DC-DC conversion
- Secondary side synchronous rectifier
- Isolated converter primary side switch
- Motor control

3 Description

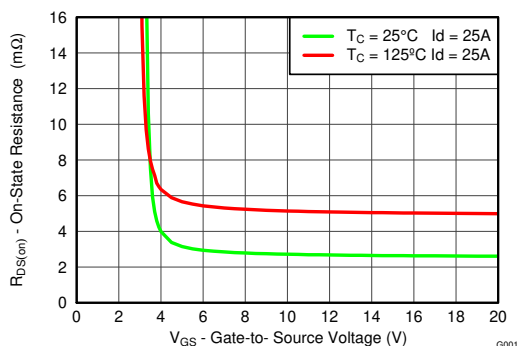
This 2.5mΩ, 60V SON 5mm × 6mm NexFET™ power MOSFET is designed to minimize losses in power conversion applications.



Top View

Product Summary

$T_A = 25^\circ\text{C}$		TYPICAL VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	60	V
Q_g	Gate Charge Total (10V)	44	nC
Q_{gd}	Gate Charge Gate-to-Drain	6.9	nC



$R_{DS(on)}$ vs V_{GS}

Product Summary (continued)

$T_A = 25^\circ\text{C}$		TYPICAL VALUE	UNIT
$R_{DS(on)}$	Drain-to-Source On-Resistance	$V_{GS} = 4.5\text{V}$	3.3
		$V_{GS} = 10\text{V}$	2.5
$V_{GS(th)}$	Threshold Voltage	1.8	V

Package Information

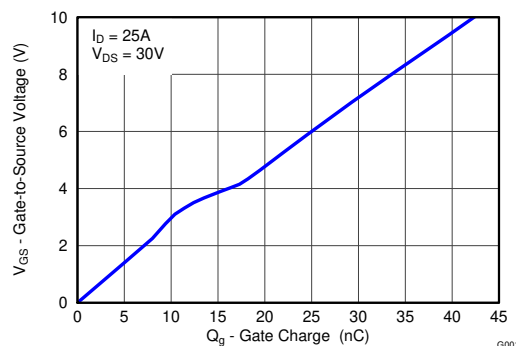
DEVICE	QTY	MEDIA	PACKAGE ^{(1) (2)}	SHIP
CSD18532Q5B	2500	13-Inch Reel	SON	Tape and Reel
CSD18532Q5BT	250	13-Inch Reel	5.00mm × 6.00mm Plastic Package	

- (1) For all available packages, see the orderable addendum at the end of the datasheet.
- (2) The package size (length × width) is a nominal value and includes pins, where applicable.

Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	60	V
V_{GS}	Gate-to-Source Voltage	±20	V
I_D	Continuous Drain Current (Package Limited)	100	A
	Continuous Drain Current (Silicon Limited), $T_C = 25^\circ\text{C}$	172	
	Continuous Drain Current ⁽¹⁾	23	
I_{DM}	Pulsed Drain Current ⁽²⁾	400	A
P_D	Power Dissipation ⁽¹⁾	3.2	W
	Power Dissipation, $T_C = 25^\circ\text{C}$	156	
T_J	Operating Junction Temperature	–55 to 150	$^\circ\text{C}$
T_{stg}	Storage Temperature		
E_{AS}	Avalanche Energy, Single Pulse $I_D = 80\text{A}$, $L = 0.1\text{mH}$, $R_G = 25\Omega$	320	mJ

- (1) Typical $R_{\theta JA} = 40^\circ\text{C/W}$ on a 1-in², 2oz Cu pad on a 0.06-in thick FR4 PCB.
- (2) Maximum $R_{\theta JC} = 0.8^\circ\text{C/W}$, pulse duration ≤ 100 μs, duty cycle ≤ 1%.



Gate Charge



Table of Contents

1 Features	1	5.2 Documentation Support.....	7
2 Applications	1	5.3 Receiving Notification of Documentation Updates.....	7
3 Description	1	5.4 Support Resources.....	7
4 Specifications	3	5.5 Trademarks.....	7
4.1 Electrical Characteristics.....	3	5.6 Electrostatic Discharge Caution.....	7
4.2 Thermal Information.....	3	5.7 Glossary.....	7
4.3 Typical MOSFET Characteristics.....	4	6 Revision History	7
5 Device and Documentation Support	7	7 Mechanical, Packaging, and Orderable Information	8
5.1 Third-Party Products Disclaimer.....	7		

4 Specifications

4.1 Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise stated

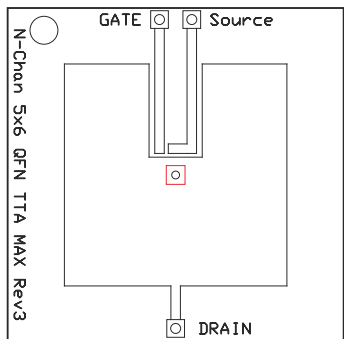
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV _{DSS}	Drain-to-source voltage	V _{GS} = 0V, I _D = 250μA	60			V
I _{DSS}	Drain-to-source leakage current	V _{GS} = 0V, V _{DS} = 48V			1	μA
I _{GSS}	Gate-to-source leakage current	V _{DS} = 0V, V _{GS} = 20V			100	nA
V _{GS(th)}	Gate-to-source threshold voltage	V _{DS} = V _{GS} , I _D = 250μA	1.5	1.8	2.2	V
R _{DS(on)}	Drain-to-source on-resistance	V _{GS} = 4.5V, I _D = 25A			3.3	mΩ
		V _{GS} = 10V, I _D = 25A			2.5	
g _{fs}	Transconductance	V _{DS} = 30V, I _D = 25A	143			S
DYNAMIC CHARACTERISTICS						
C _{iss}	Input capacitance	V _{GS} = 0V, V _{DS} = 30V, f = 1MHz		3900	5070	pF
C _{oss}	Output capacitance			470	611	pF
C _{rss}	Reverse transfer capacitance			13	17	pF
R _G	Series gate resistance			1.2	2.4	Ω
Q _g	Gate charge total (10V)	V _{DS} = 30V, I _D = 25A		44	58	nC
Q _{gd}	Gate charge gate-to-drain			6.9		nC
Q _{gs}	Gate charge gate-to-source			10		nC
Q _{g(th)}	Gate charge at V _{th}			6.3		nC
Q _{oss}	Output charge	V _{DS} = 30V, V _{GS} = 0V		52		nC
t _{d(on)}	Turnon delay time	V _{DS} = 30V, V _{GS} = 10V, I _{DS} = 25A, R _G = 0 Ω		5.8		ns
t _r	Rise time			7.2		ns
t _{d(off)}	Turnoff delay time			22		ns
t _f	Fall time			3.1		ns
DIODE CHARACTERISTICS						
V _{SD}	Diode forward voltage	I _{SD} = 25A, V _{GS} = 0V		0.8	1	V
Q _{rr}	Reverse recovery charge	V _{DS} = 30V, I _F = 25A, di/dt = 300A/μs		111		nC
t _{rr}	Reverse recovery time			49		ns

4.2 Thermal Information

$T_A = 25^\circ\text{C}$ unless otherwise stated

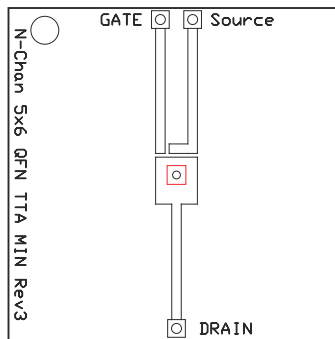
THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-case thermal resistance ⁽¹⁾			0.8	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction-to-ambient thermal resistance ^{(1) (2)}			50	$^\circ\text{C/W}$

- (1) $R_{\theta JC}$ is determined with the device mounted on a 1in² (6.45cm²), 2oz. (0.071mm) thick Cu pad on a 1.5in × 1.5in (3.81cm × 3.81cm), 0.06in (1.52mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.
- (2) Device mounted on FR4 material with 1in² (6.45cm²), 2oz (0.071mm) thick Cu.



M0137-01

Maximum $R_{\theta JA} = 50^{\circ}\text{C/W}$
when mounted on 1 in²
(6.45cm²) of 2oz (0.071mm)
thick Cu.

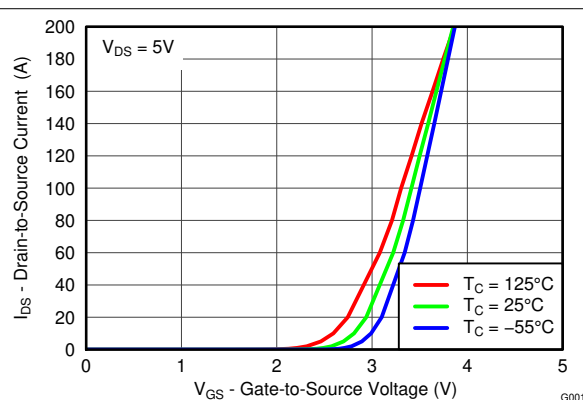
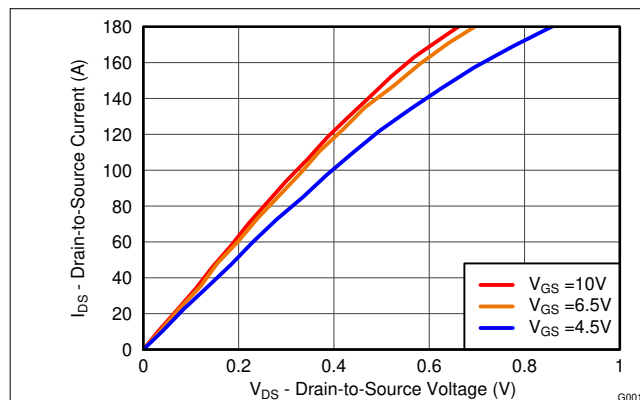
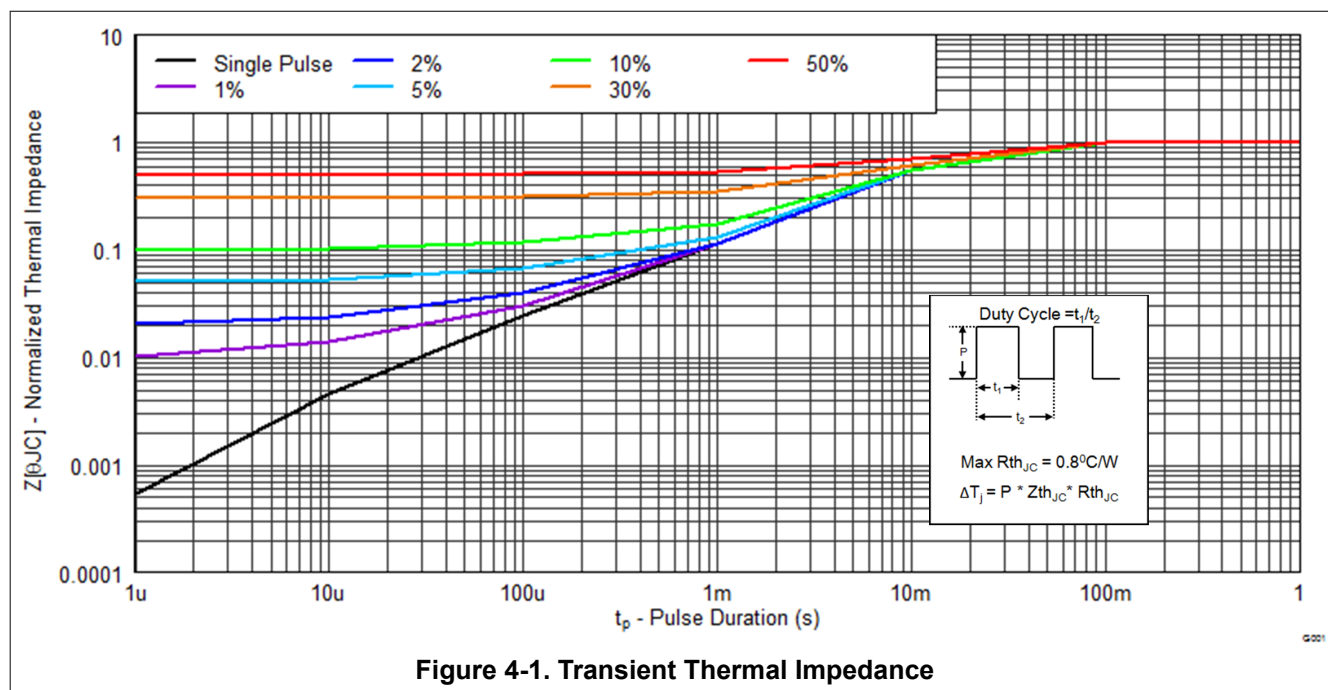


M0137-02

Maximum $R_{\theta JA} = 125^{\circ}\text{C/W}$
when mounted on a
minimum pad area of 2oz
(0.071mm) thick Cu.

4.3 Typical MOSFET Characteristics

$T_A = 25^{\circ}\text{C}$ unless otherwise stated



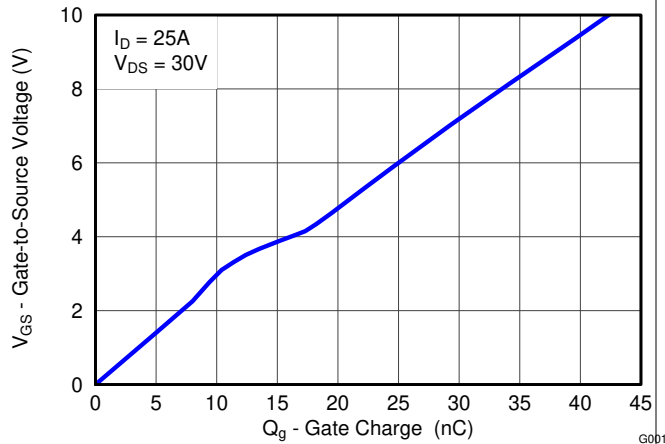


Figure 4-4. Gate Charge

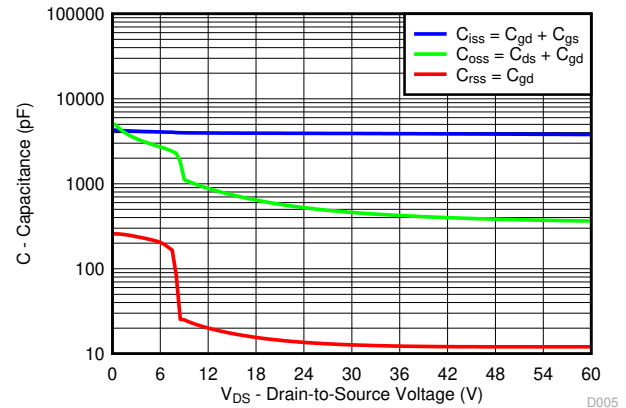


Figure 4-5. Capacitance

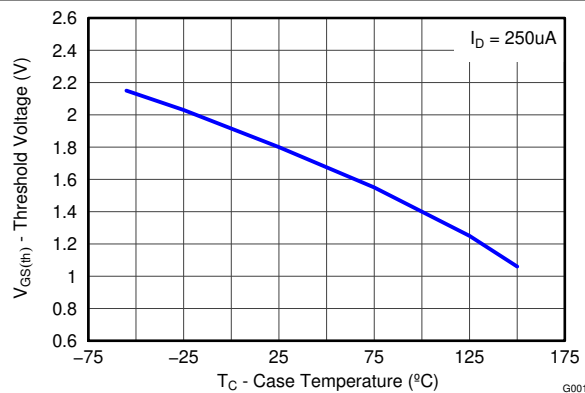


Figure 4-6. Threshold Voltage vs Temperature

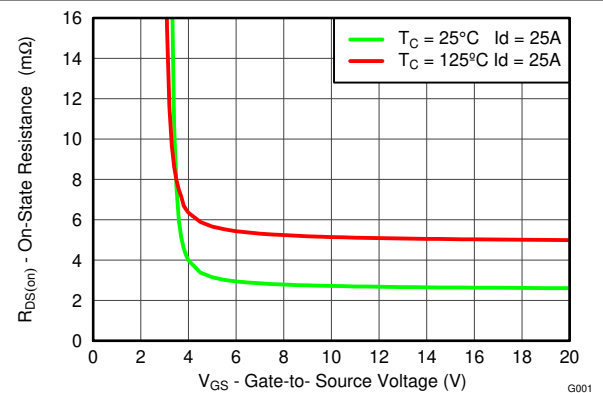


Figure 4-7. On-State Resistance vs Gate-to-Source Voltage

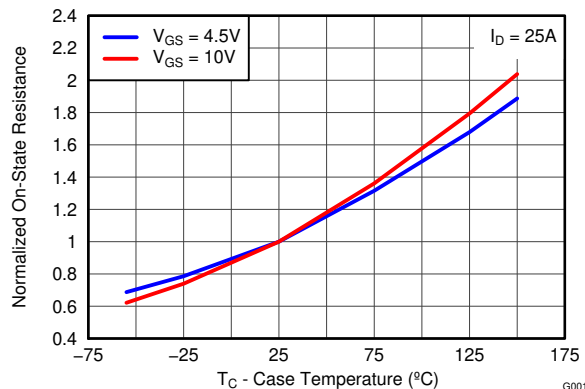


Figure 4-8. Normalized On-State Resistance vs Temperature

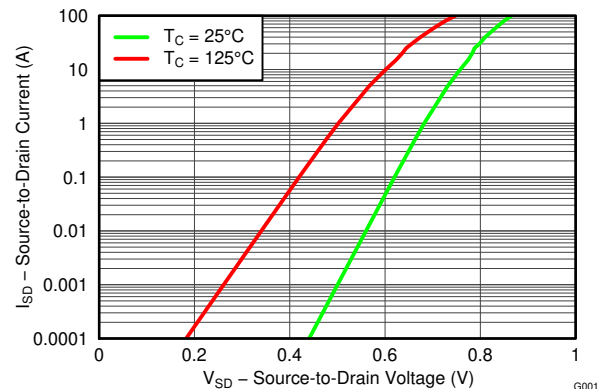


Figure 4-9. Typical Diode Forward Voltage

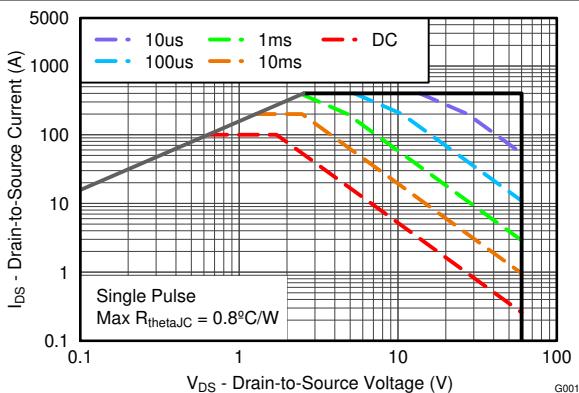


Figure 4-10. Maximum Safe Operating Area

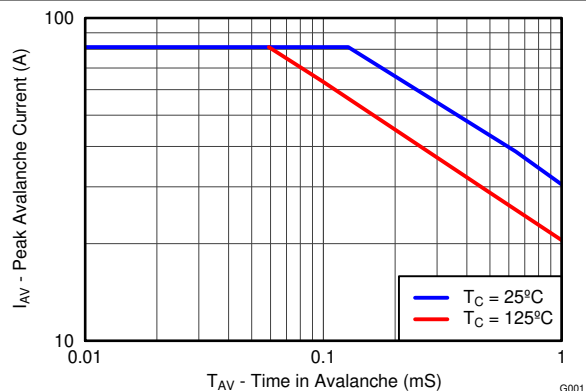


Figure 4-11. Single Pulse Unclamped Inductive Switching

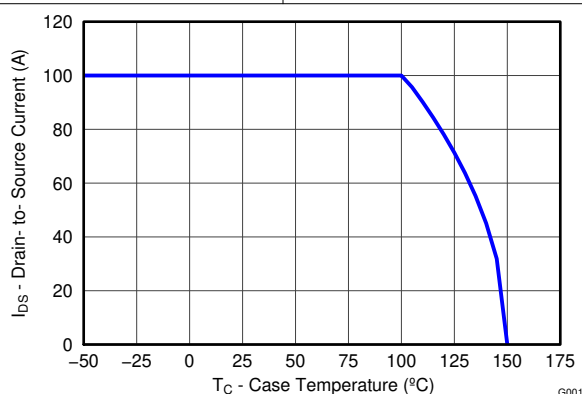


Figure 4-12. Maximum Drain Current vs Temperature

5 Device and Documentation Support

5.1 Third-Party Products Disclaimer

TI'S PUBLICATION OF INFORMATION REGARDING THIRD-PARTY PRODUCTS OR SERVICES DOES NOT CONSTITUTE AN ENDORSEMENT REGARDING THE SUITABILITY OF SUCH PRODUCTS OR SERVICES OR A WARRANTY, REPRESENTATION OR ENDORSEMENT OF SUCH PRODUCTS OR SERVICES, EITHER ALONE OR IN COMBINATION WITH ANY TI PRODUCT OR SERVICE.

5.2 Documentation Support

5.2.1 Related Documentation

5.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

5.4 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

5.5 Trademarks

NexFET™ and TI E2E™ are trademarks of Texas Instruments.

is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

5.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

5.7 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

6 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision D (February 2018) to Revision E (July 2026)	Page
• Updated the numbering format for tables, figures, and cross-references throughout the document.....	1

Changes from Revision C (May 2017) to Revision D (February 2018)	Page
• Extended the V_{DS} on Figure 4-5 to 60V.....	4

7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
CSD18532Q5B	Active	Production	VSON-CLIP (DNK) 8	2500 LARGE T&R	ROHS Exempt	NIPDAU SN	Level-1-260C-UNLIM	-55 to 150	CSD18532
CSD18532Q5B.B	Active	Production	VSON-CLIP (DNK) 8	2500 LARGE T&R	ROHS Exempt	NIPDAU	Level-1-260C-UNLIM	-55 to 150	CSD18532
CSD18532Q5BG4	Active	Production	VSON-CLIP (DNK) 8	2500 LARGE T&R	ROHS Exempt	NIPDAU	Level-1-260C-UNLIM	-55 to 150	CSD18532
CSD18532Q5BG4.B	Active	Production	VSON-CLIP (DNK) 8	2500 LARGE T&R	ROHS Exempt	NIPDAU	Level-1-260C-UNLIM	-55 to 150	CSD18532
CSD18532Q5BT	Active	Production	VSON-CLIP (DNK) 8	250 SMALL T&R	ROHS Exempt	NIPDAU SN	Level-1-260C-UNLIM	-55 to 150	CSD18532
CSD18532Q5BT.B	Active	Production	VSON-CLIP (DNK) 8	250 SMALL T&R	ROHS Exempt	NIPDAU	Level-1-260C-UNLIM	-55 to 150	CSD18532

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

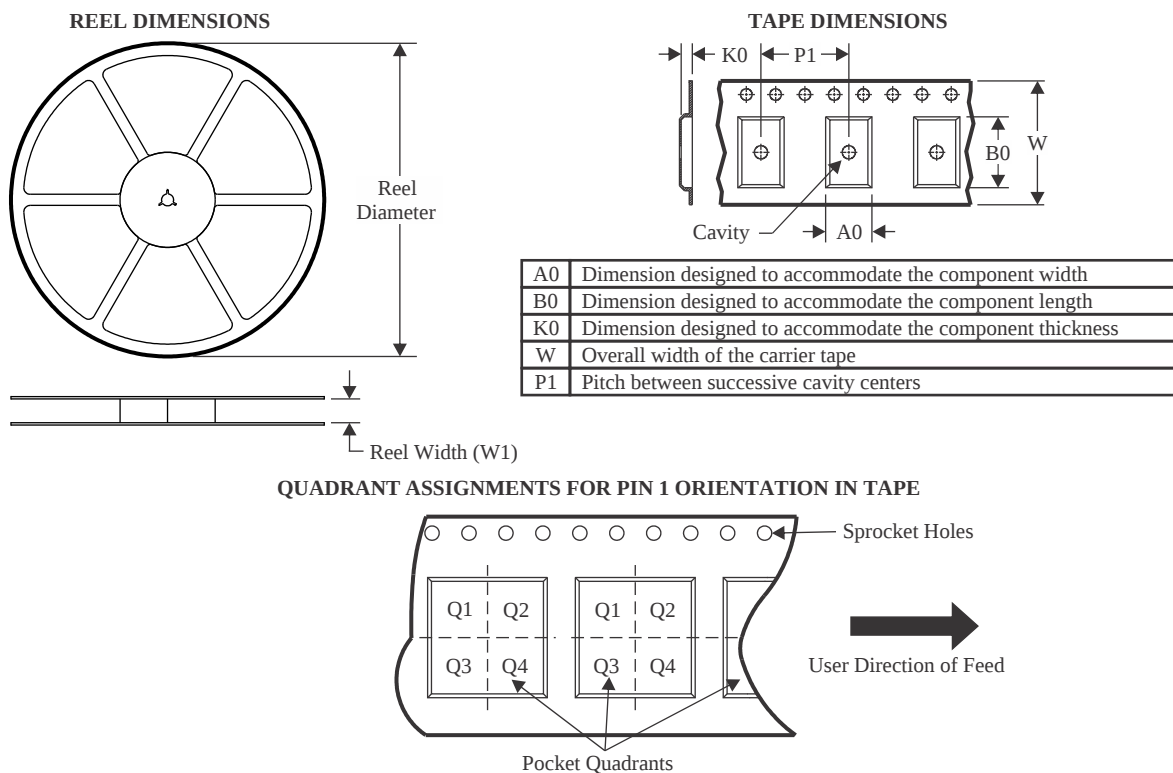
⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

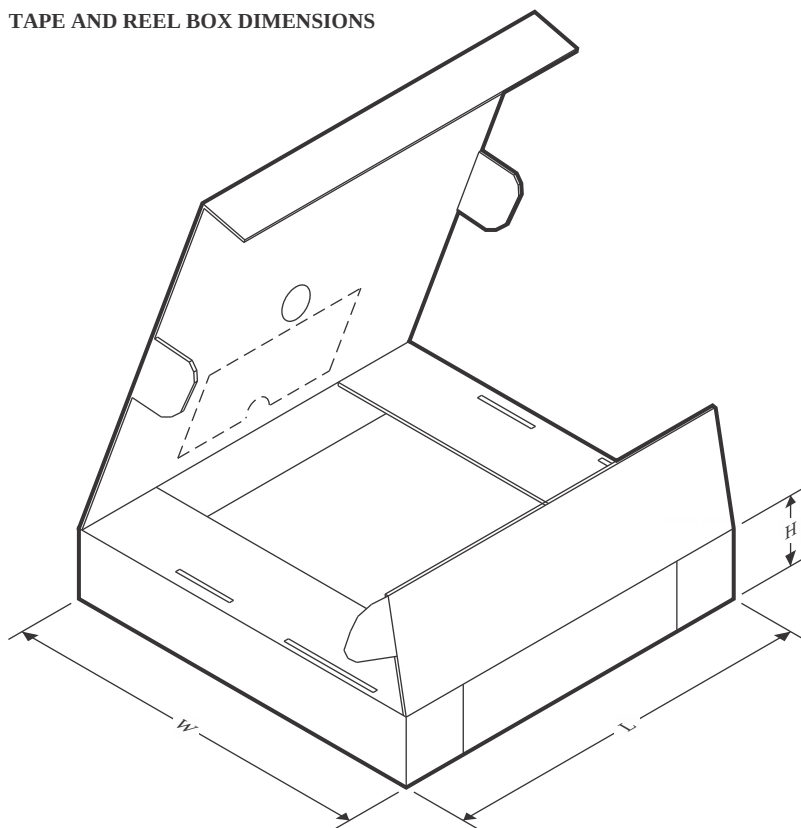
TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD18532Q5B	VSON-CLIP	DNK	8	2500	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1
CSD18532Q5BG4	VSON-CLIP	DNK	8	2500	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1
CSD18532Q5BT	VSON-CLIP	DNK	8	250	180.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

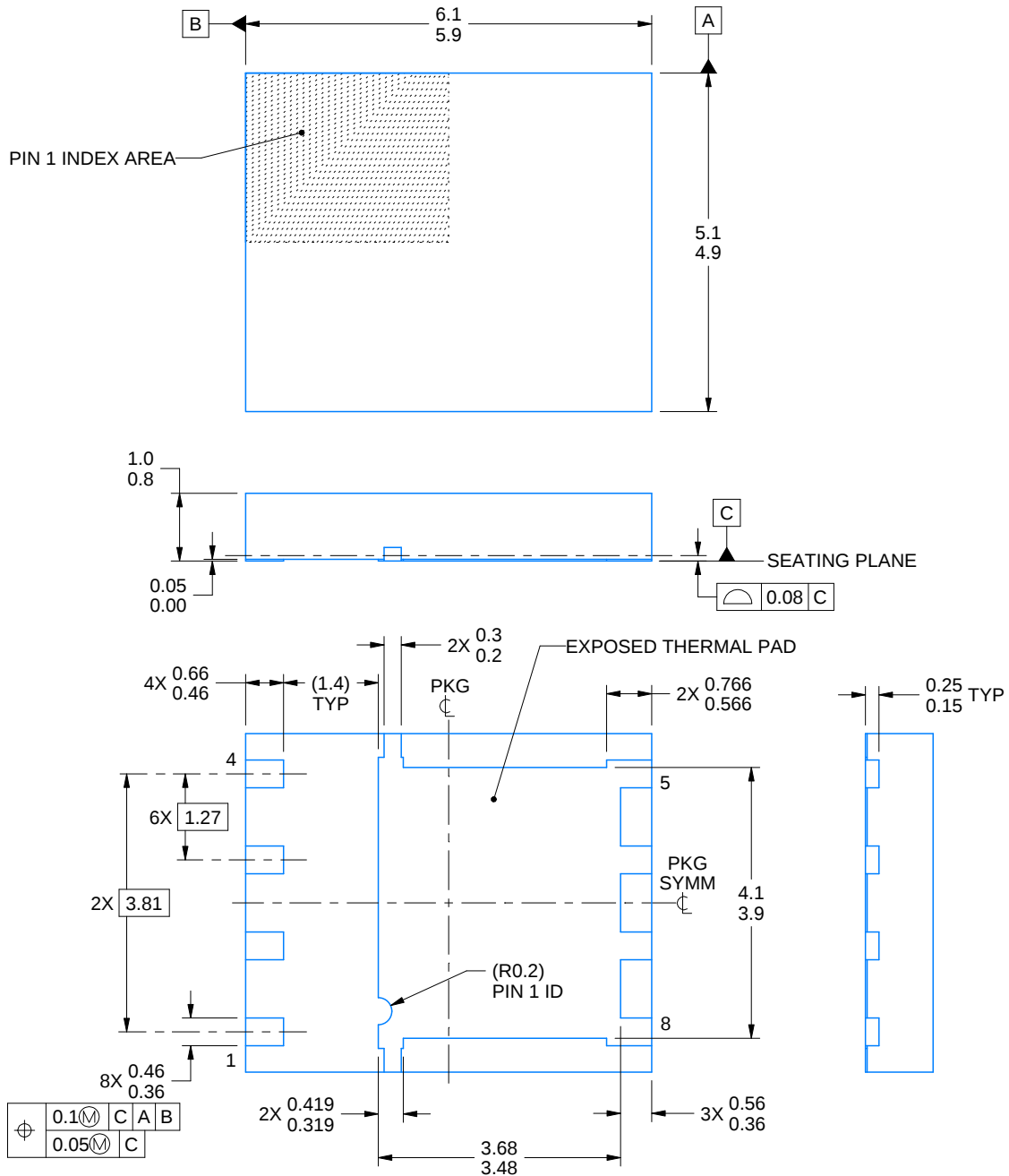
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD18532Q5B	VSON-CLIP	DNK	8	2500	346.0	346.0	33.0
CSD18532Q5BG4	VSON-CLIP	DNK	8	2500	346.0	346.0	33.0
CSD18532Q5BT	VSON-CLIP	DNK	8	250	182.0	182.0	20.0

PACKAGE OUTLINE

DNK0008A

VSON-CLIP - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



4226669/A 04/2021

NOTES:

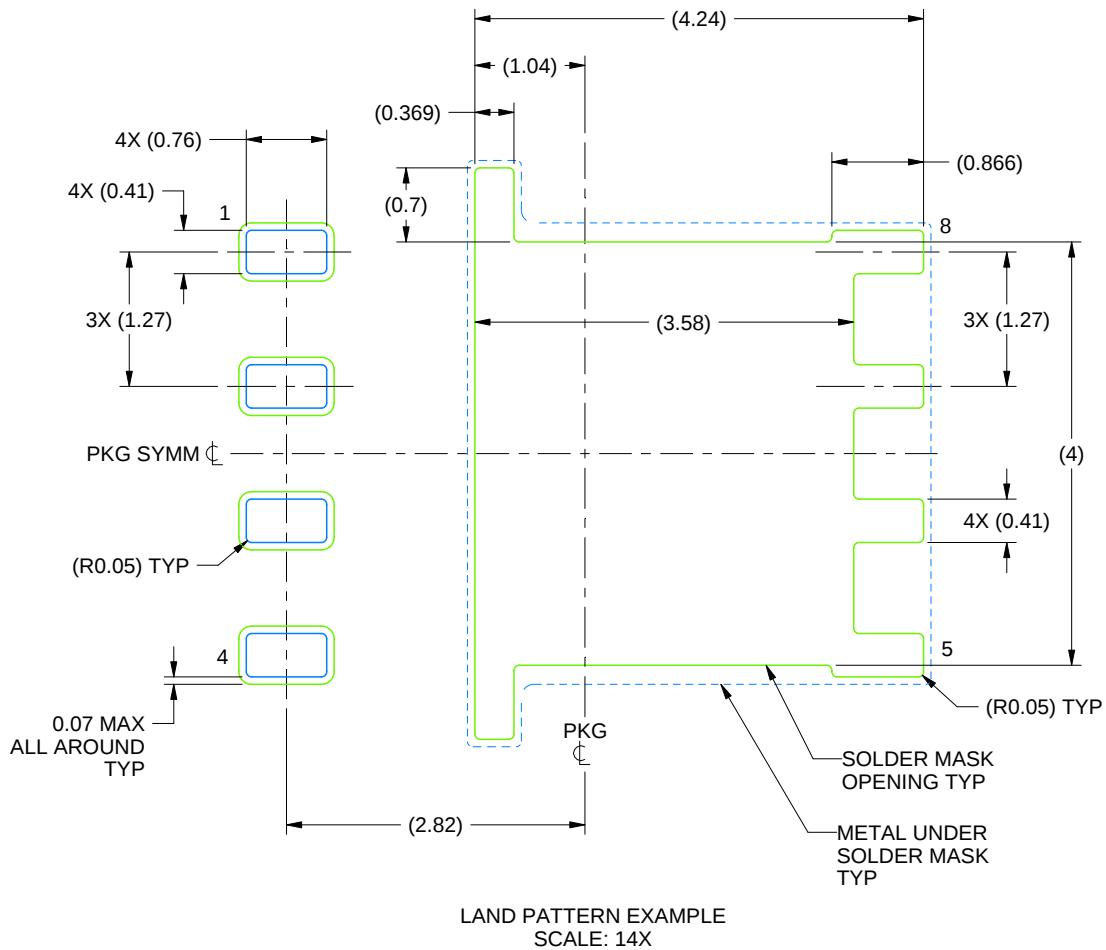
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

EXAMPLE BOARD LAYOUT

DNK0008A

VSON-CLIP - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



4226669/A 04/2021

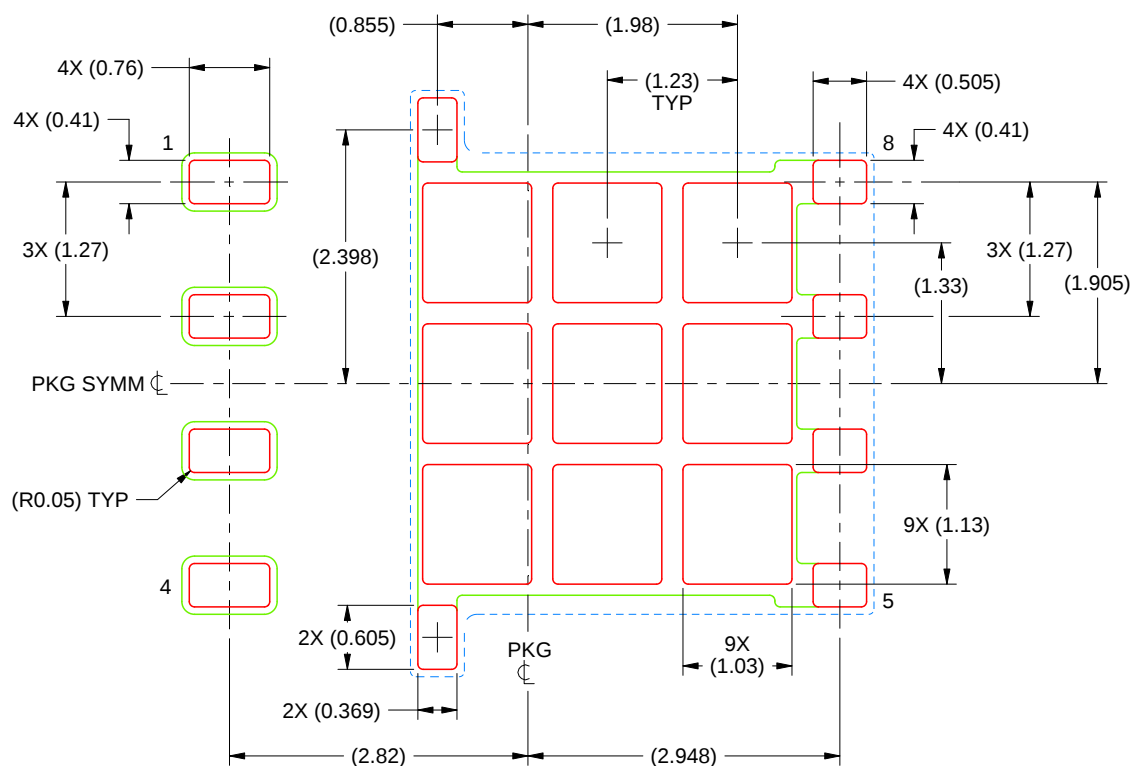
NOTES: (continued)

- This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).
- Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.

DNK0008A

VSON-CLIP - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 14X

74% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE

4226669/A 04/2021

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you fully indemnify TI and its representatives against any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to [TI's Terms of Sale](#), [TI's General Quality Guidelines](#), or other applicable terms available either on [ti.com](#) or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products. Unless TI explicitly designates a product as custom or customer-specified, TI products are standard, catalog, general purpose devices.

TI objects to and rejects any additional or different terms you may propose.

Copyright © 2026, Texas Instruments Incorporated

Last updated 10/2025